MBR2080CTG, MBR2090CTG, MBR20100CTG

Switch-mode Power Rectifiers

This series uses the Schottky Barrier principle with a platinum barrier metal. These state-of-the-art devices have the following features:

Features

- 20 A Total (10 A Per Diode Leg)
- Guard-Ring for Stress Protection
- Low Forward Voltage
- 175°C Operating Junction Temperature
- Epoxy Meets UL 94 V-0 @ 0.125 in
- Low Power Loss/High Efficiency
- High Surge Capacity
- Low Stored Charge Majority Carrier Conduction
- Shipped 50 units per plastic tube
- These Devices are Pb-Free and are RoHS Compliant*

Mechanical Characteristics:

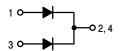
- Case: Epoxy, Molded
- Weight: 1.9 grams (approximately)
- Finish: All External Surfaces Corrosion Resistant and Terminal Leads are Readily Solderable
- Lead Temperature for Soldering Purposes: 260°C Max. for 10 Seconds



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SCHOTTKY BARRIER RECTIFIERS 20 AMPERES 80-100 VOLTS





TO-220 CASE 221A STYLE 6

MARKING DIAGRAM



A = Assembly Location

Y = Year
WW = Work Week
B20x0 = Device Code
x = 8, 9 or 10
G = Pb-Free Device
AKA = Polarity Designator

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 2 of this data sheet.

^{*}For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

MBR2080CTG, MBR2090CTG, MBR20100CTG

MAXIMUM RATINGS (Per Diode Leg)

		MBR			
Rating	Symbol	2080CT	2090CT	20100CT	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V _{RRM} V _{RWM} V _R	80	90	100	V
Average Rectified Forward Current (Rated V _R) T _C = 133°C	I _{F(AV)}		10		А
Peak Repetitive Forward Current (Rated V _R , Square Wave, 20 kHz) T _C = 133°C	I _{FRM}		20		А
Nonrepetitive Peak Surge Current (Surge applied at rated load conditions halfwave, single phase, 60 Hz)	I _{FSM}	150		A	
Peak Repetitive Reverse Surge Current (2.0 μs, 1.0 kHz)	I _{RRM}		0.5		Α
Operating Junction Temperature (Note 1)	TJ		-65 to +17	5	°C
Storage Temperature	T _{stg}	- 65 to +175		°C	
Voltage Rate of Change (Rated V _R)	dv/dt		10,000		V/μs

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

THERMAL CHARACTERISTICS

Characteristic	Symbol	Value	Unit
Maximum Thermal Resistance Junction-to-Case Junction-to-Ambient	$R_{ heta JC} \ R_{ heta JA}$	2.0 60	°C/W

ELECTRICAL CHARACTERISTICS (Per Diode Leg)

,			
Characteristic	Symbol	Value	Unit
Maximum Instantaneous Forward Voltage (Note 2) ($i_F = 10 \text{ Amps}$, $T_C = 125^{\circ}\text{C}$) ($i_F = 10 \text{ Amps}$, $T_C = 25^{\circ}\text{C}$) ($i_F = 20 \text{ Amps}$, $T_C = 125^{\circ}\text{C}$) ($i_F = 20 \text{ Amps}$, $T_C = 25^{\circ}\text{C}$)	VF	0.75 0.85 0.85 0.95	V
Maximum Instantaneous Reverse Current (Note 2) (Rated dc Voltage, T_C = 125°C) (Rated dc Voltage, T_C = 25°C)	İR	6.0 0.1	mA

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

ORDERING INFORMATION

Device	Package	Shipping
MBR2080CTG	TO-220 (Pb-Free)	50 Units / Rail
MBR2090CTG	TO-220 (Pb-Free)	50 Units / Rail
MBR20100CTG	TO-220 (Pb-Free)	50 Units / Rail

^{1.} The heat generated must be less than the thermal conductivity from Junction–to–Ambient: $dP_D/dT_J < 1/R_{\theta JA}$.

^{2.} Pulse Test: Pulse Width = 300 μ s, Duty Cycle \leq 2.0%.

MBR2080CTG, MBR2090CTG, MBR20100CTG

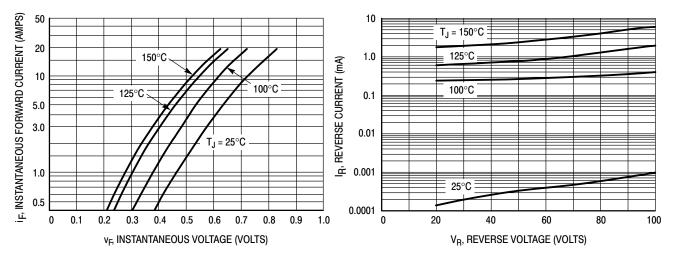


Figure 1. Typical Forward Voltage Per Diode

Figure 2. Typical Reverse Current Per Diode

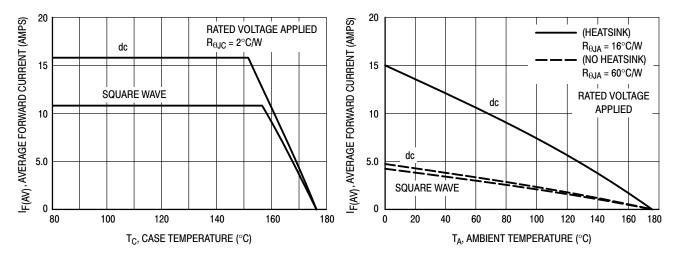


Figure 3. Typical Current Derating, Case, Per Leg

Figure 4. Typical Current Derating, Ambient, Per Leg

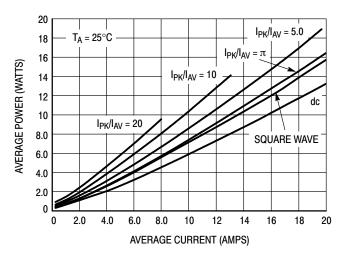
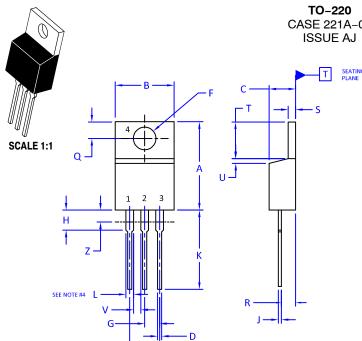


Figure 5. Average Power Dissipation and Average Current

MECHANICAL CASE OUTLINE



CASE 221A-09

DATE 05 NOV 2019

NOTES:

- 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 2009.
- 2. CONTROLLING DIMENSION: INCHES
- 3. DIMENSION Z DEFINES A ZONE WHERE ALL BODY AND LEAD IRREGULARITIES ARE ALLOWED.

4. MAX WIDTH FOR F102 DEVICE = 1.35MM

	INCHES		MILLIMETERS		
DIM	MIN.	MAX.	MIN.	MAX.	
Α	0.570	0.620	14.48	15.75	
В	0.380	0.415	9.66	10.53	
С	0.160	0.190	4.07	4.83	
D	0.025	0.038	0.64	0.96	
F	0.142	0.161	3.60	4.09	
G	0.095	0.105	2.42	2.66	
Н	0.110	0.161	2.80	4.10	
J	0.014	0.024	0.36	0.61	
К	0.500	0.562	12.70	14.27	
L	0.045	0.060	1.15	1.52	
N	0.190	0.210	4.83	5.33	
Q	0.100	0.120	2.54	3.04	
R	0.080	0.110	2.04	2.79	
S	0.045	0.055	1.15	1.41	
Т	0.235	0.255	5.97	6.47	
U	0.000	0.050	0.00	1.27	
V	0.045		1.15		
Z		0.080		2.04	

STYLE 1:		STYLE 2:		STYLE 3:		STYLE 4:	
PIN 1.	BASE	PIN 1.	BASE	PIN 1.	CATHODE	PIN 1.	MAIN TERMINAL 1
2.	COLLECTOR	2.	EMITTER	2.	ANODE	2.	MAIN TERMINAL 2
3.	EMITTER	3.	COLLECTOR	3.	GATE	3.	GATE
4.	COLLECTOR	4.	EMITTER	4.	ANODE	4.	MAIN TERMINAL 2
STYLE 5:		STYLE 6:		STYLE 7:		STYLE 8:	
PIN 1.	GATE	PIN 1.	ANODE	PIN 1.	CATHODE	PIN 1.	CATHODE
2.	DRAIN	2.	CATHODE	2.	ANODE	2.	ANODE
3.	SOURCE	3.	ANODE	3.	CATHODE	3.	EXTERNAL TRIP/DELAY
4.	DRAIN	4.	CATHODE	4.	ANODE	4.	ANODE
STYLE 9:		STYLE 10:		STYLE 11	:	STYLE 12	:
PIN 1.	GATE	PIN 1.	GATE	PIN 1.	DRAIN	PIN 1.	MAIN TERMINAL 1
2.	COLLECTOR	2.	SOURCE	2.	SOURCE	2.	MAIN TERMINAL 2
3.	EMITTER	3.	DRAIN	3.	GATE	3.	GATE
4.	COLLECTOR	4.	SOURCE	4.	SOURCE	4.	NOT CONNECTED

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FAN3111ESX FDMC86262P FDMD8530 FEBFL7733A_L53U021A FEBFOD8333 MM74HC138MX MMBZ5233B FOD3120SD
FPAB30BH60B FQP2N80 1.5KE16AG MT9V115EBKSTCH-GEVB NB6L295MNGEVB NB7L1008MNGEVB NC7WZ126K8X
NCL30000LED2GEVB NCN9252MUGEVB NCP1075PSRGEVB NCV4274CDT33RKG NCV887100D1R2G NDT2955 1N5339B
NSIC2030JBT3G NV890231MWTXGEVB CAT4101AEVB KA7818ETU S3JB 2SC5569-TD-E FEBFL7734_L55L008A 1V5KE39CA
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